ON Semiconductor®

FFSH15120ADN-F155

Silicon Carbide Schottky Diode
1200 V, 15 A

Features

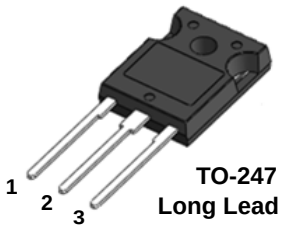
- Max Junction Temperature 175 °C
- Avalanche Rated 80 mJ
- High Surge Current Capacity
- Positive Temperature Coefficient
- Ease of Paralleling
- No Reverse Recovery / No Forward Recovery

Applications

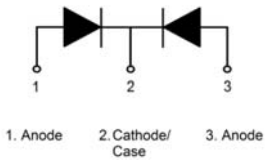
- General Purpose
- SMPS, Solar Inverter, UPS
- Power Switching Circuits

Description

Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability compared to Silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size and cost.



TO-247
Long Lead



Absolute Maximum Ratings T_C = 25 °C unless otherwise noted. (per leg)

Symbol	Parameter		FFSH15120ADN-F155	Unit
V_{RRM}	Peak Repetitive Reverse Voltage		1200	V
E_{AS}	Single Pulse Avalanche Energy (Note 1)		80	mJ
I_F	Continuous Rectified Forward Current @ T_C < 148 °C		8* / 15**	A
$I_{F, Max}$	Non-Repetitive Peak Forward Surge Current	T_C = 25 °C, 10 µs	560	A
		T_C = 150 °C, 10 µs	500	A
$I_{F,SM}$	Non-Repetitive Forward Surge Current	Half-Sine Pulse, t_p = 8.3 ms	80	A
$I_{F,RM}$	Repetitive Forward Surge Current	Half-Sine Pulse, t_p = 8.3 ms	36	A
Ptot	Power Dissipation	T_C = 25 °C	110	W
		T_C = 150 °C	19	W
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +175	°C
	TO247 Mounting Torque, M3 Screw		60	Ncm

Thermal Characteristic

Symbol	Parameter	FFSH15120ADN-F155	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max	1.35* / 0.56**	°C/W

* Per leg, ** Per Device

September-2017, Rev. 2

Publication Order Number:
FFSH15120ADN-F155/D

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FFSH15120ADN-F155	FFSH15120ADN	TO-247 Long Lead	Tube	N/A	N/A	30 units

Electrical Characteristics T_C = 25 °C unless otherwise noted. (per leg)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V_F	Forward Voltage	I_F = 8 A, T_C = 25 °C	-	1.45	1.75	V
		I_F = 8 A, T_C = 125 °C	-	1.7	2	
		I_F = 8 A, T_C = 175 °C	-	2	2.4	
I_R	Reverse Current	V_R = 1200 V, T_C = 25 °C	-	-	200	µA
		V_R = 1200 V, T_C = 125 °C	-	-	300	
		V_R = 1200 V, T_C = 175 °C	-	-	400	
Q_C	Total Capacitive Charge	V = 800 V	-	55	-	nC
C	Total Capacitance	V_R = 1 V, f = 100 kHz	-	538	-	pF
		V_R = 400 V, f = 100 kHz	-	50	-	
		V_R = 800 V, f = 100 kHz	-	40	-	

Notes:
1: EAS of 80 mJ is based on starting T_J = 25 °C, L = 0.5 mH, I_{AS} = 18 A, V = 150 V.

Typical Characteristics T_J = 25 °C unless otherwise noted (per leg).

Figure 1. Forward Characteristics

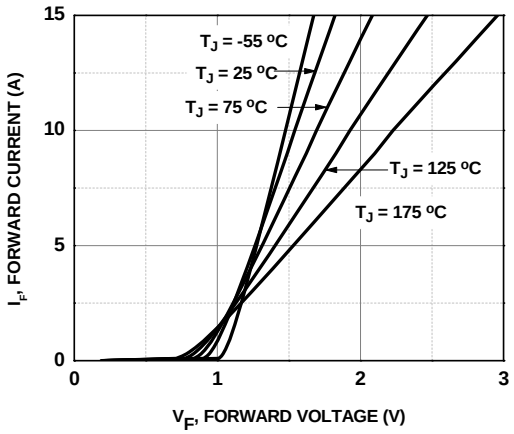


Figure 2. Reverse Characteristics

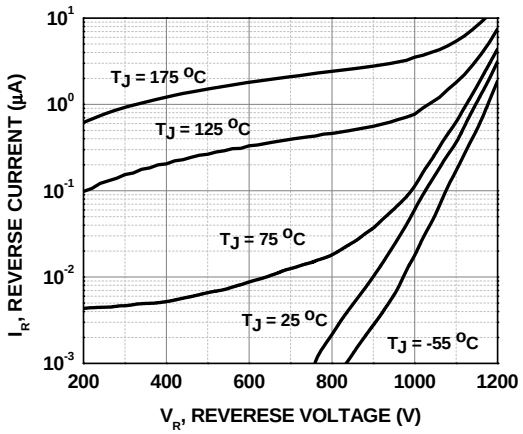


Figure 3. Reverse Characteristics

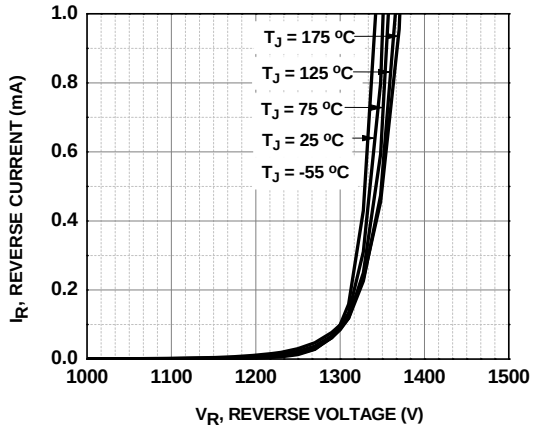
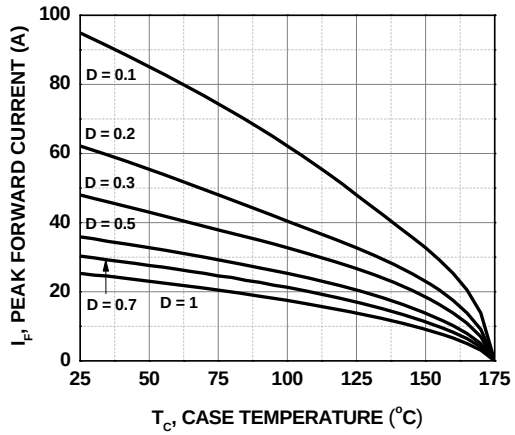


Figure 4. Current Derating



Typical Characteristics T_J = 25 °C unless otherwise noted (per leg, continue).

Figure 5. Power Derating

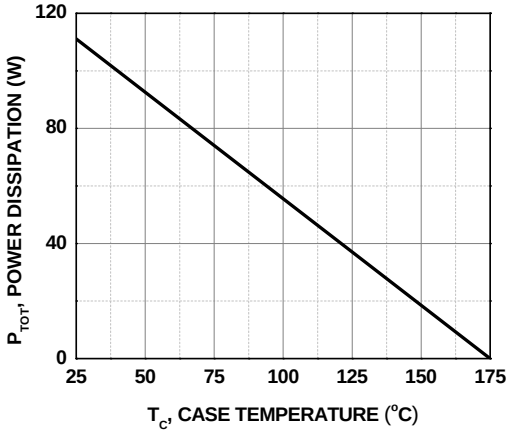


Figure 6. Capacitive Charge vs. Reverse Voltage

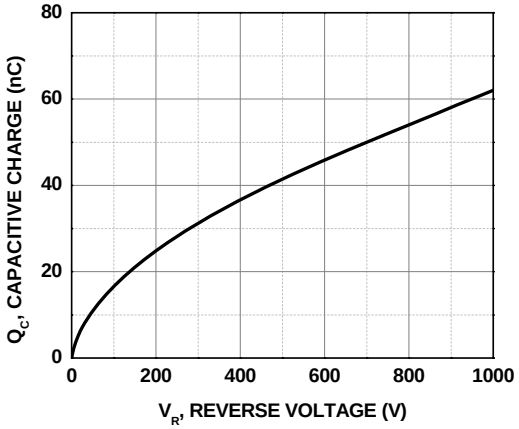


Figure 7. Capacitance vs. Reverse Voltage

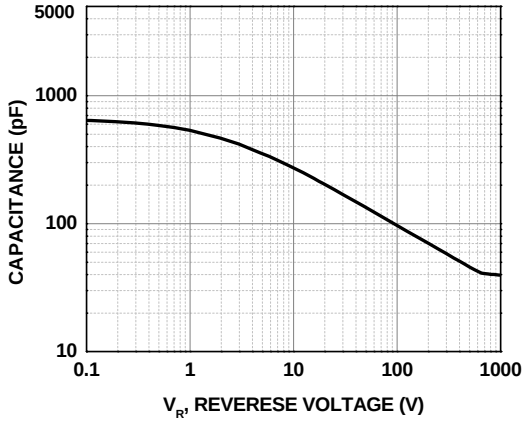


Figure 8. Capacitance Stored Energy

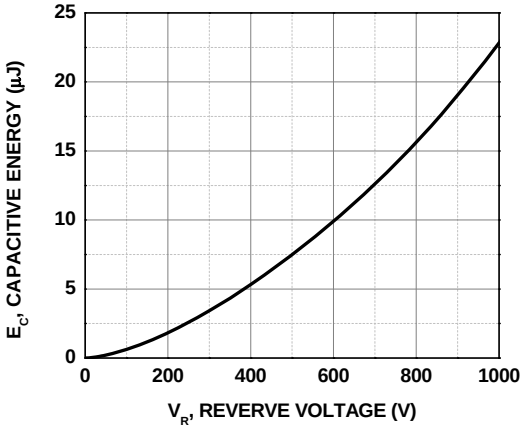
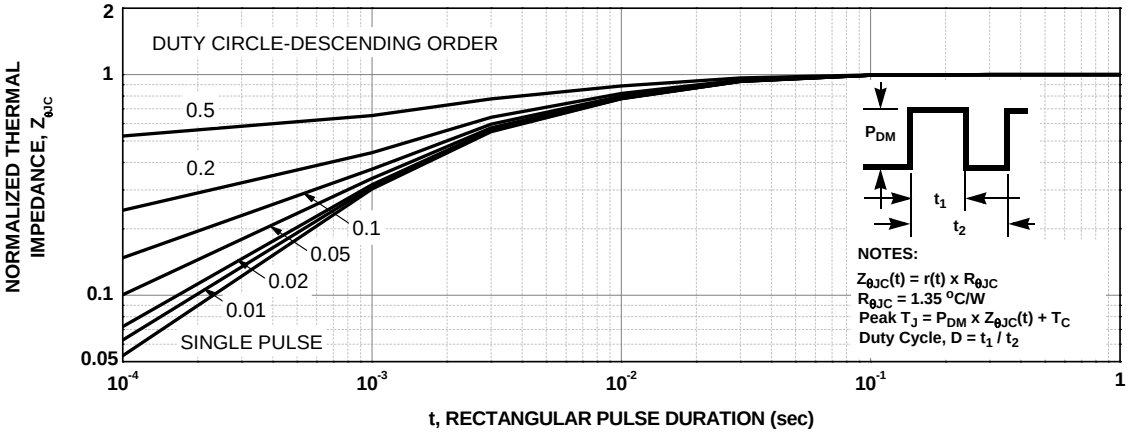
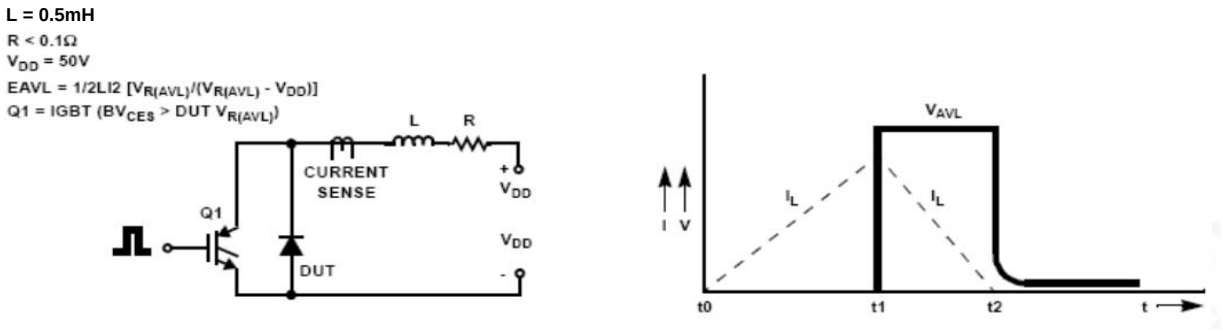


Figure 9. Junction-to-Case Transient Thermal Response Curve



Test Circuit and Waveforms

Figure 10. Unclamped Inductive Switching Test Circuit & Waveform



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